

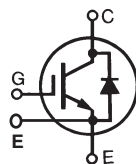


**THE DATASHEET OF
IXXN110N65B4H1**



XPT™ 650V GenX4™ IXXN110N65B4H1 w/ Sonic Diode

Extreme Light Punch Through
IGBT for 10-30kHz Switching



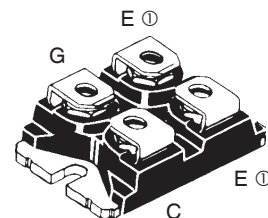
$$V_{CES} = 650V$$

$$I_{C110} = 110A$$

$$V_{CE(sat)} \leq 2.10V$$

$$t_{fi(typ)} = 43ns$$

SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
Ⓢ either emitter terminal can be used as
Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	650	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	230	A
I_{C25}	Terminal Current Limit	200	A
I_{C110}	$T_C = 110^\circ C$	110	A
I_{F110}	$T_C = 110^\circ C$	70	A
I_{CM}	$T_C = 25^\circ C$, 1ms	650	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 220$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$ $R_G = 82\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ C$	750	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
V_{ISOL}	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- 2500V~ Isolation Voltage
- Anti-Parallel Sonic Diode
- Optimized for 10-30kHz Switching
- Square RBSOA
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

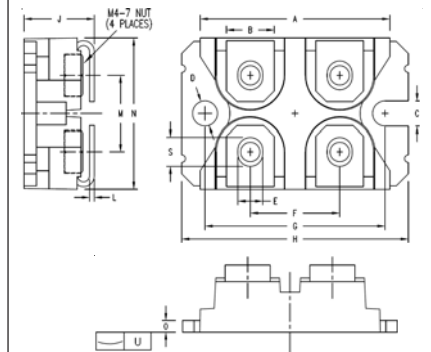
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 110A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.72 2.05	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	30	52	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3650	pF
C_{oes}			470	pF
C_{res}			80	pF
Q_g	$I_C = 110\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		183	nC
Q_{ge}			32	nC
Q_{gc}			83	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 55\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		26	ns
t_{ri}			40	ns
E_{on}			2.20	mJ
$t_{d(off)}$			146	ns
t_{fi}			43	ns
E_{off}			1.05	1.70 mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 55\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		25	ns
t_{ri}			40	ns
E_{on}			3.00	mJ
$t_{d(off)}$			140	ns
t_{fi}			110	ns
E_{off}			2.16	mJ
R_{thJC}			0.20	$^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

SOT-227B miniBLOC (IXXN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

Reverse Sonic Diode (FRD)

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 100\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.7 1.8	V V
I_{RM}	$I_F = 100\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C}$ $-di_F/dt = 1500\text{A}/\mu\text{s}, V_R = 300\text{V}$		95	A
t_{rr}			100	ns
R_{thJC}			0.42	$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

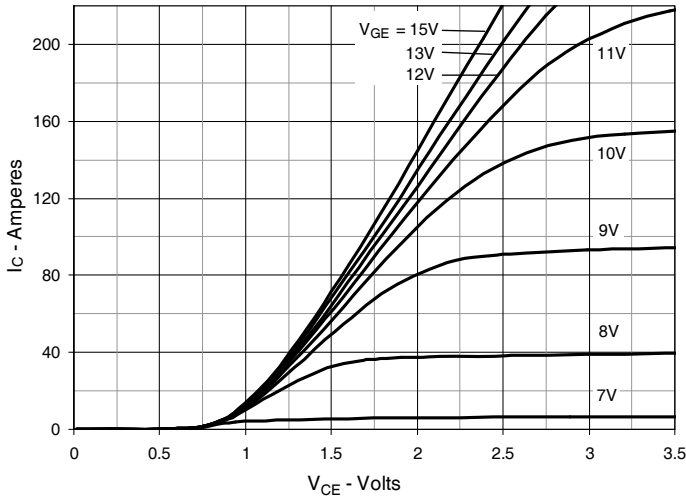


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

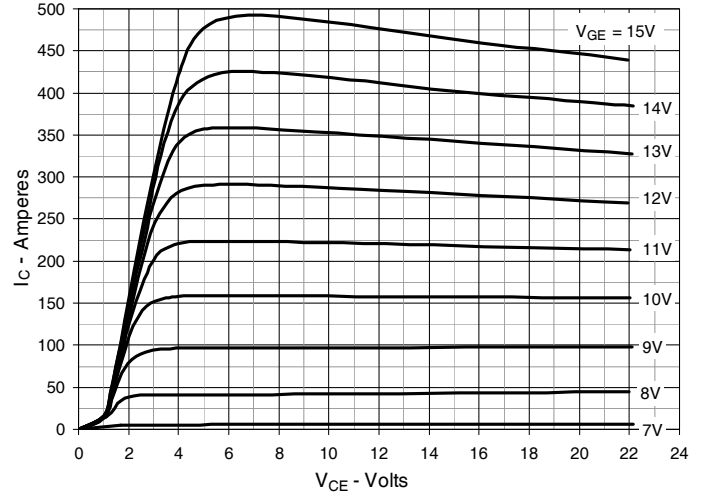


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

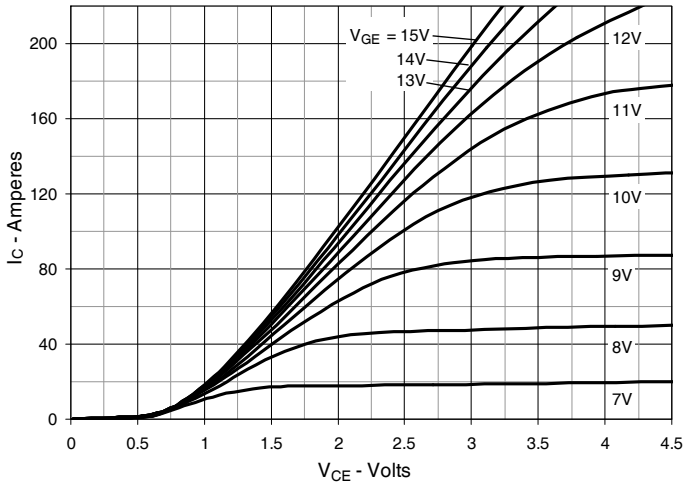


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

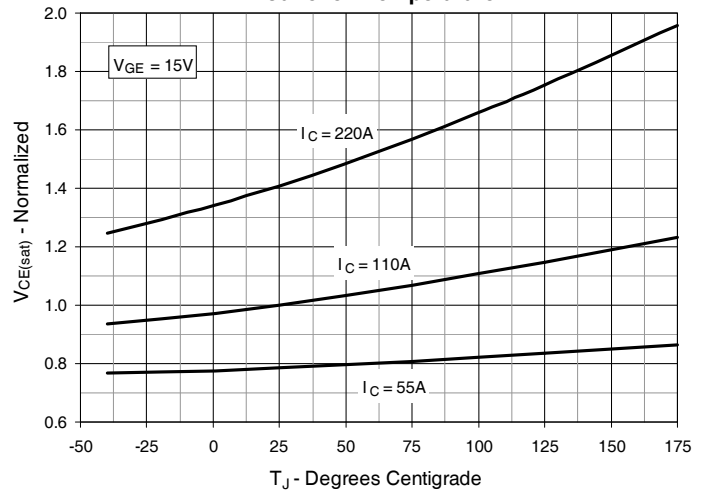


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

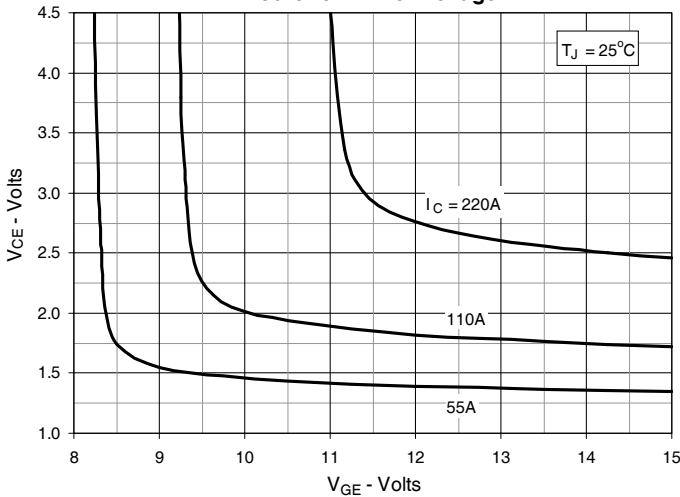


Fig. 6. Input Admittance

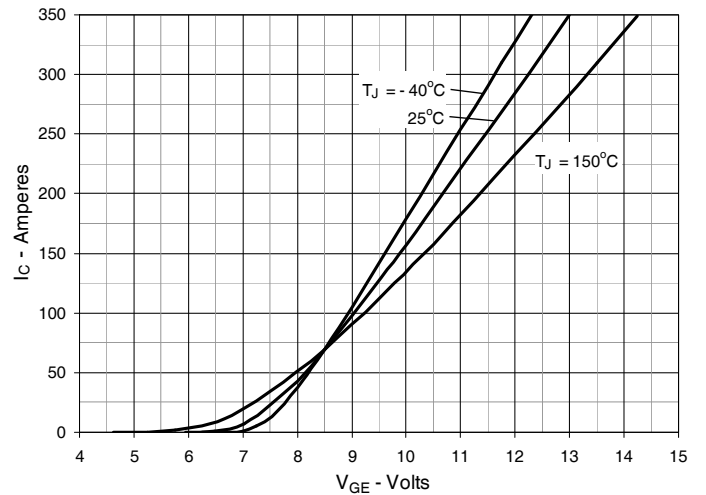


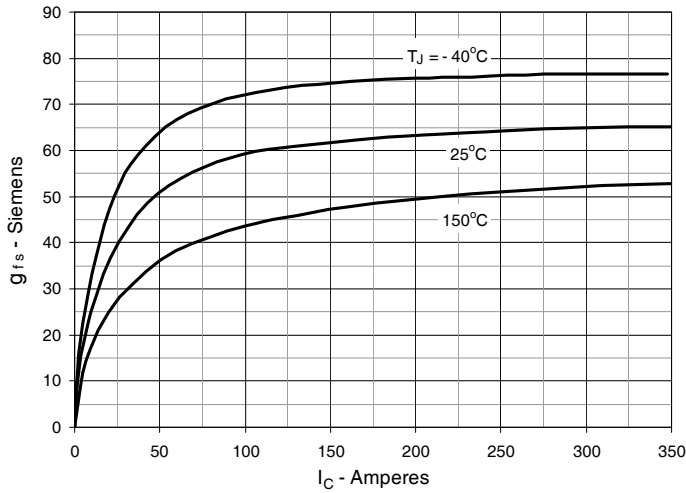
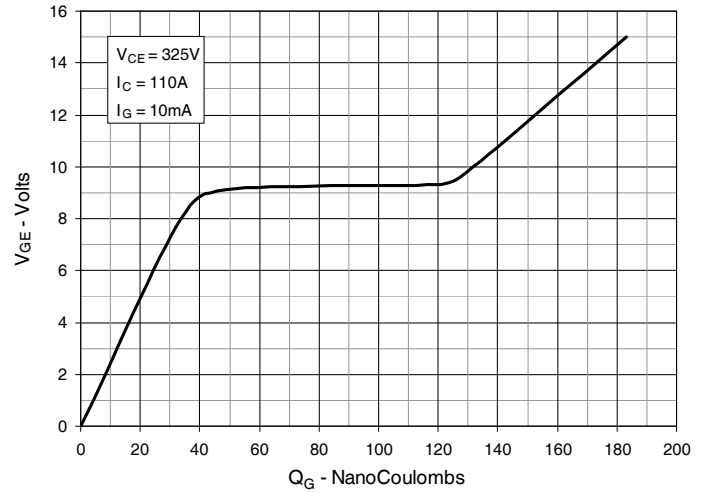
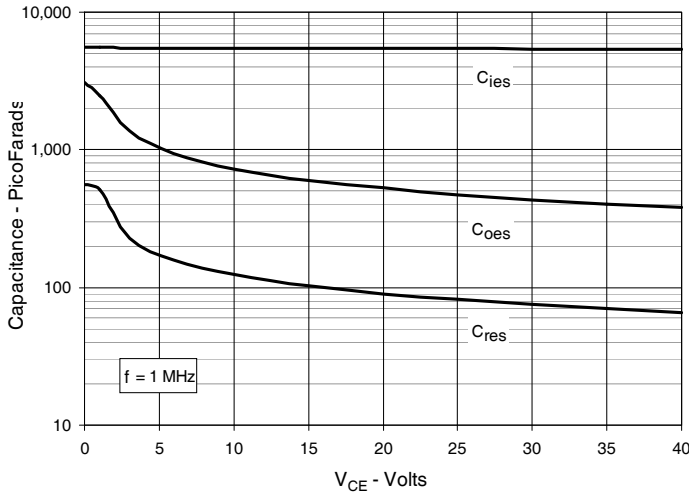
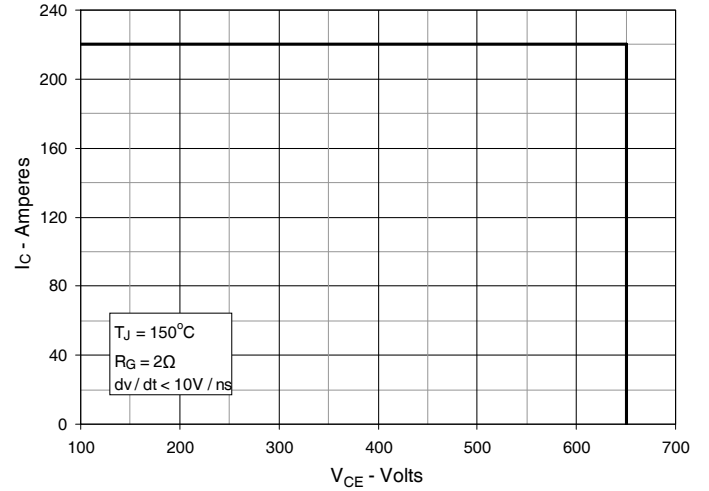
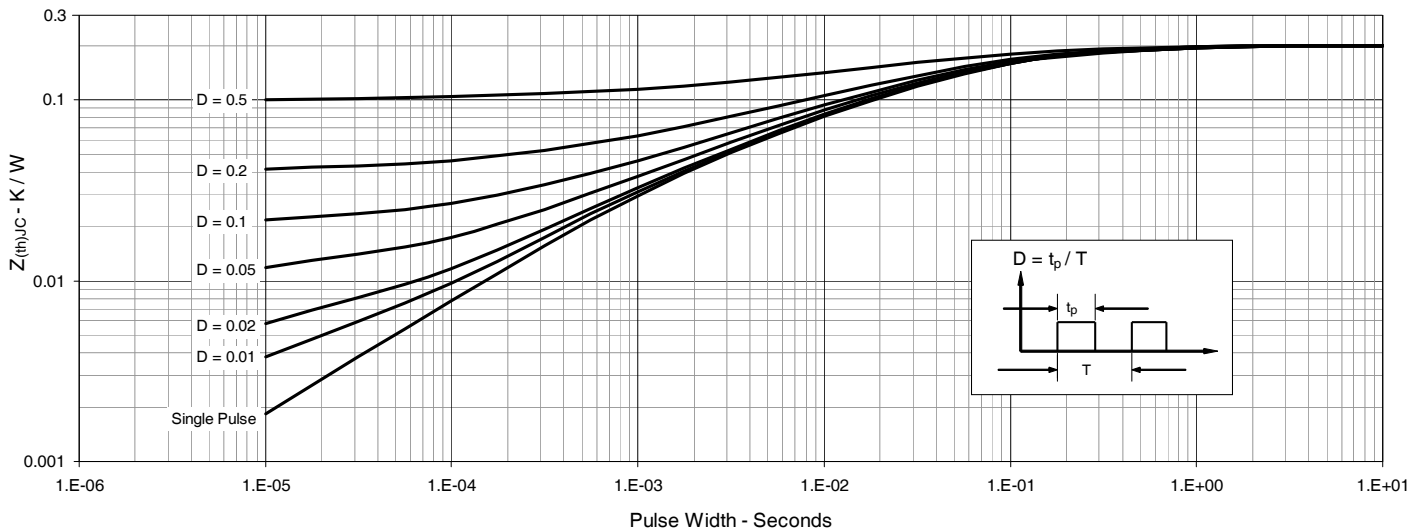
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance (IGBT)


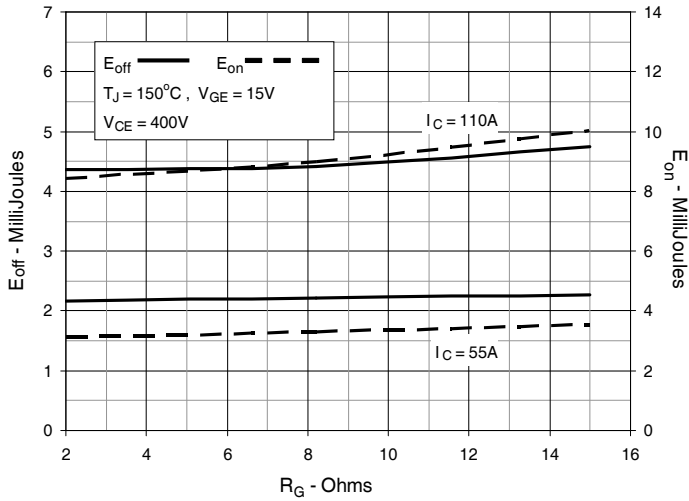
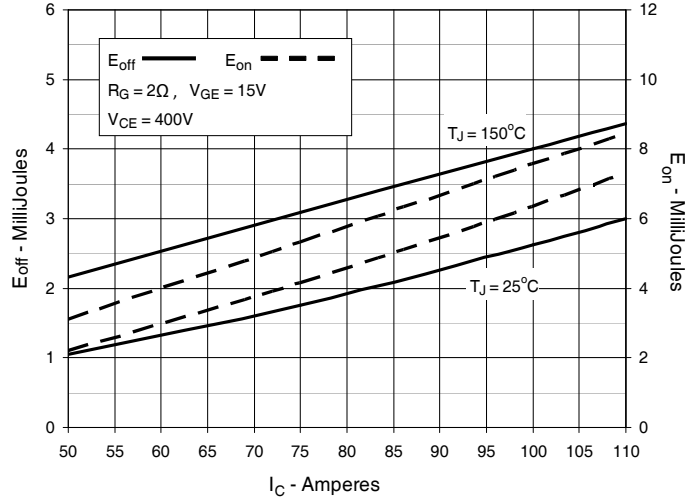
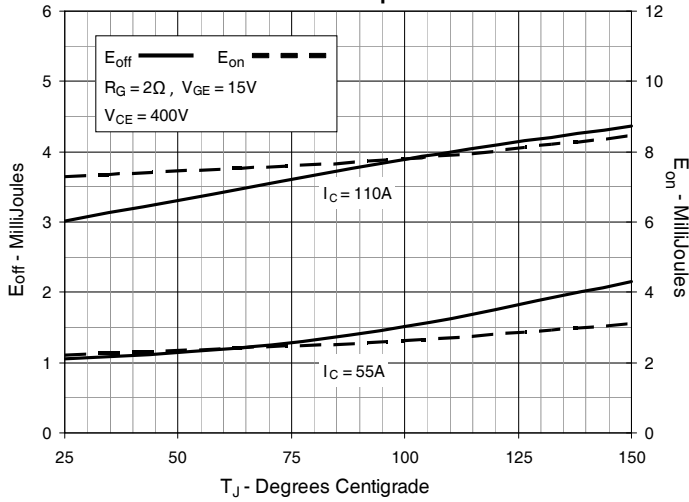
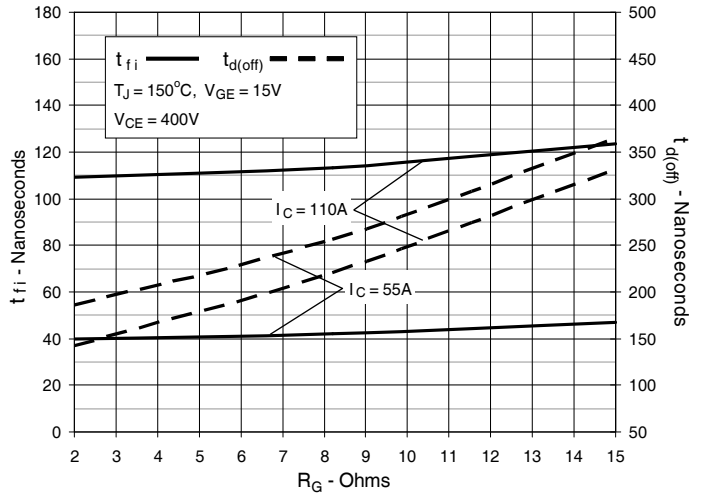
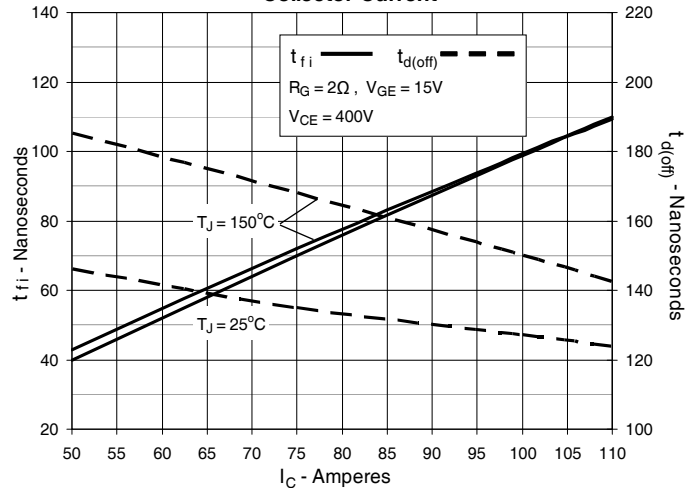
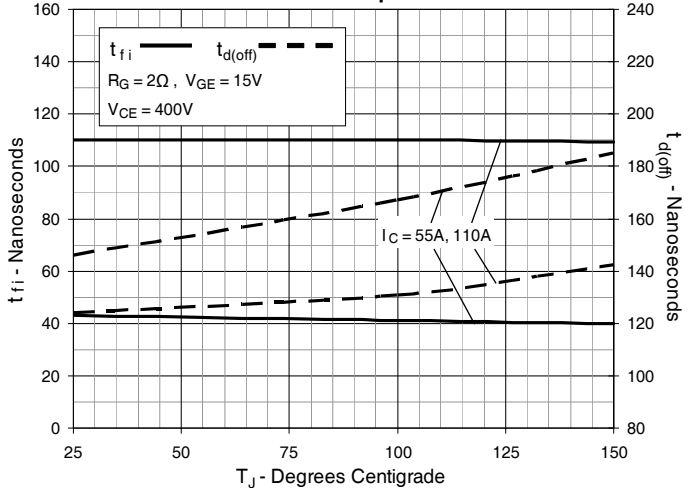
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


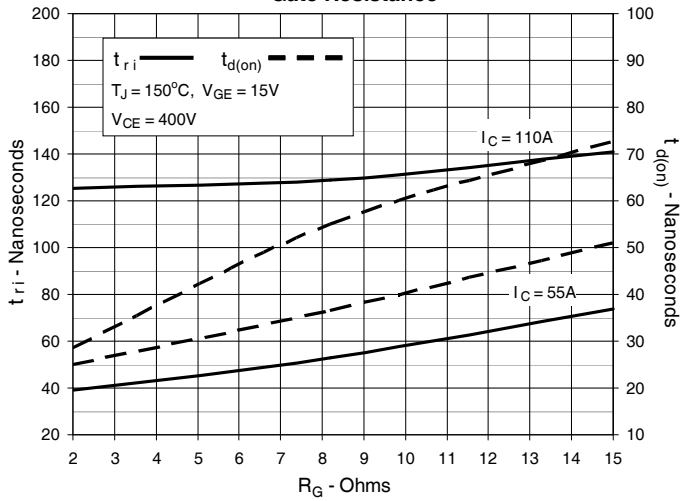
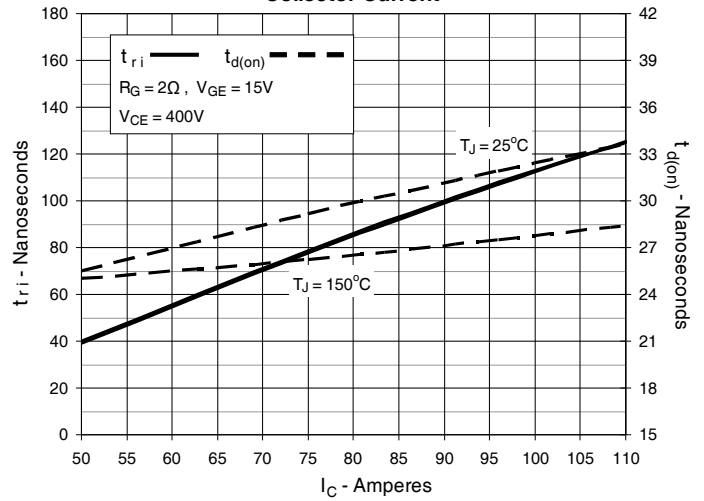
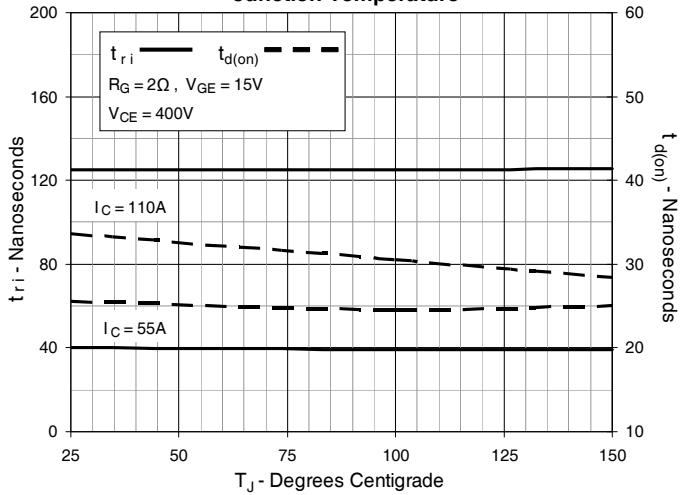
Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature


Fig. 21. Typ. Forward characteristics

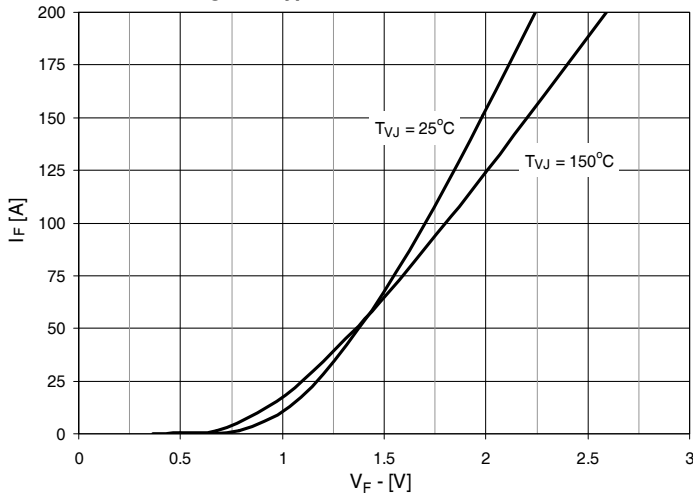


Fig. 22. Typ. Reverse Recovery Charge Q_{rr} vs. $-di_F/dt$

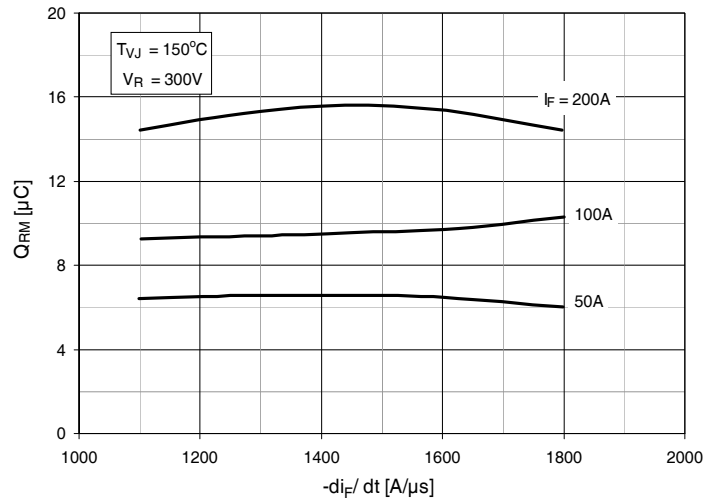


Fig. 23. Typ. Peak Reverse Current I_{RM} vs. $-di_F/dt$

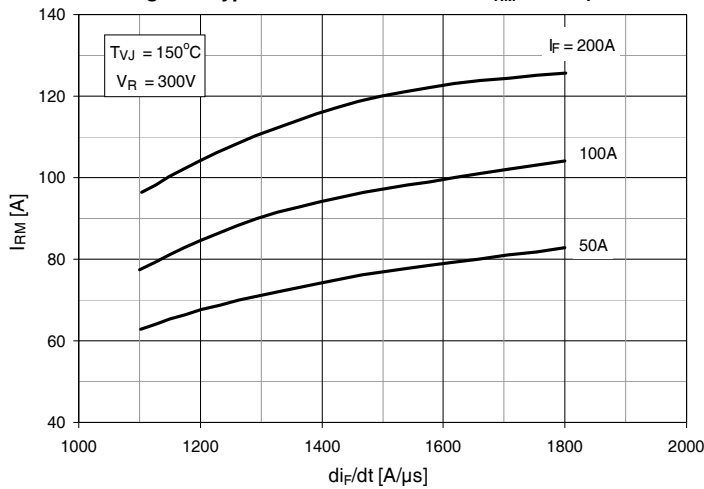


Fig. 24. Typ. Recovery Time t_{rr} vs. $-di_F/dt$

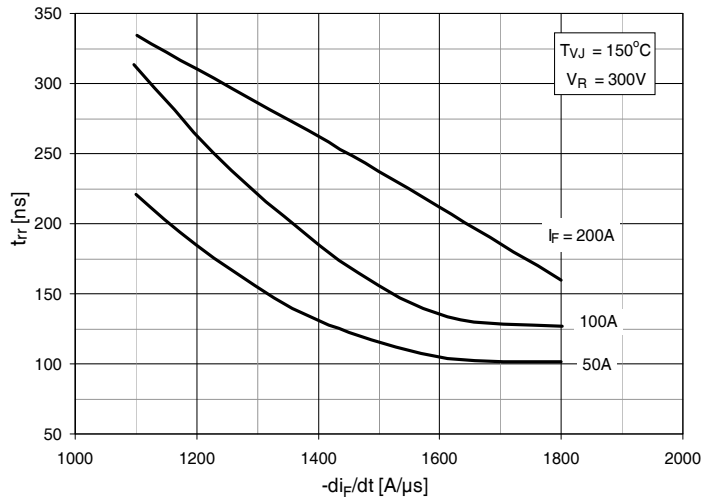


Fig. 25. Typ. Recovery Energy E_{rec} vs. $-di_F/dt$

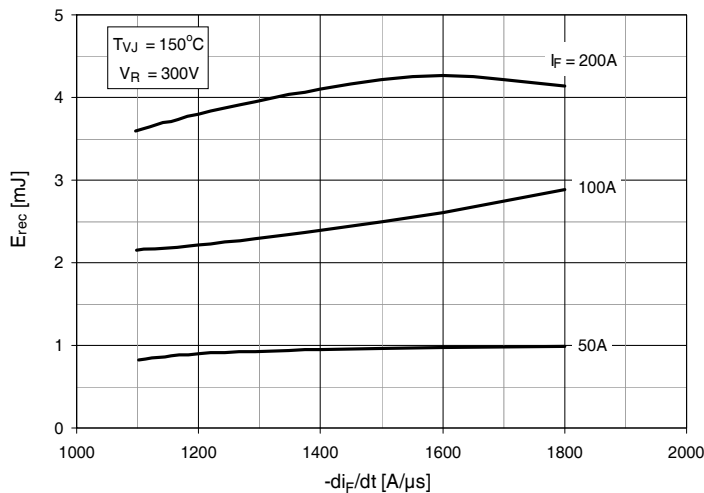
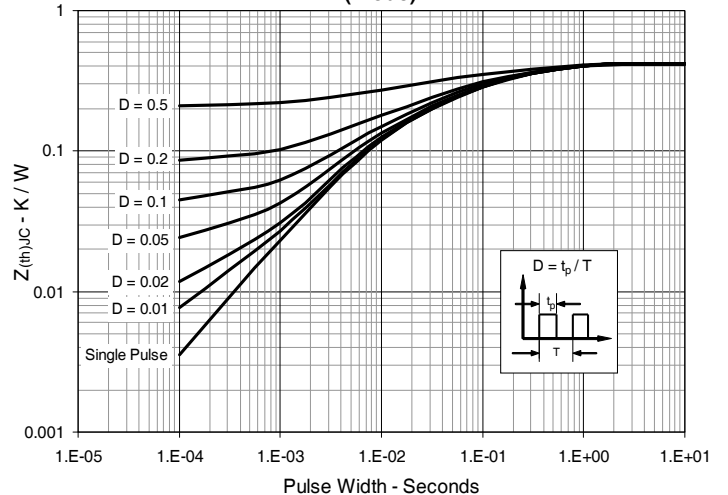


Fig. 26. Maximum Transient Thermal Impedance (Diode)





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